

C1  
Cont.

electrode positioned to put the dielectric film therebetween; and  
a silicon oxide film residing on top of the capacitor to form a planarized surface;  
wherein nitrogen resides over the planarized surface of the silicon oxide film; and  
wherein the contact is positioned above the silicon oxide film including nitrogen.

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subD1  
C2

5. (Thrice Amended) A semiconductor device, comprising:  
a contact;  
a transistor having a first impurity region and a second impurity region formed on a semiconductor substrate, and a gate electrode formed on the semiconductor substrate;  
a first insulating film residing on top of the transistor;  
a capacitor formed on the first insulating film, the capacitor having a dielectric made of one of ferroelectric material and a high-dielectric material, and an upper electrode and a lower electrode positioned to put the dielectric film therebetween;  
a second insulating film formed on the capacitor;  
a local interconnection formed on the second insulating film to electrically connecting the upper electrode of the capacitor with the first impurity region;  
a third insulating film formed on the local interconnection and the second insulating film;  
a first wiring formed on the third insulating film and electrically connected to the second impurity region via a hole which is formed on the first insulating film, the second insulating film, and the third insulating film;  
a fourth insulating film on top of the first wiring to serve an upper planarized surface,

C2  
Cont.

wherein nitrogen resides on top of the upper planarized surface of the fourth insulating film;  
wherein the contact is positioned above the fourth insulating film including nitrogen; and  
a second wiring formed on the fourth insulating film.

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intro  
C3

12. (Thrice Amended) A semiconductor device, comprising:  
a contact;  
a transistor having a first impurity region and a second impurity region formed on a semiconductor substrate, and a gate electrode formed on the semiconductor substrate;  
a first insulating film on top of the transistor;  
a capacitor formed on the first insulating film, the capacitor having a dielectric film made of one of a ferroelectric material and a high-dielectric material, and an upper electrode and a lower electrode positioned to put the dielectric film therebetween;  
a second insulating film on top of the capacitor to serve as an upper planarized surface;  
wherein nitrogen resides on top of the upper planarized surface of the second insulating film;  
and  
wherein the contact is positioned above the second insulating film including nitrogen.

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